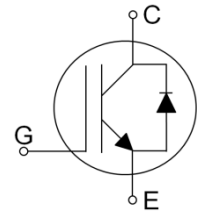


Features

- 900V Field Stop Trench Technology
- High Speed Switching
- Low Conduction Loss
- Positive Temperature Coefficient
- Easy Parallel Operation
- RoHS Compliant
- JEDEC Qualification



Applications

Induction Heating, Soft switching application

Device	Package	Marking	Remark
TGAN40N90FD	TO-3PN	TGAN40N90FD	RoHS

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-Emitter Voltage	V_{CES}	900	V	
Gate-Emitter Voltage	V_{GES}	25	V	
Continuous Collector Current	I_C	$T_C = 25\text{ }^\circ\text{C}$	80	A
		$T_C = 100\text{ }^\circ\text{C}$	40	A
Pulsed Collector Current (Note 1)	I_{CM}	120	A	
Diode Continuous Forward Current	I_F	40	A	
Power Dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}$	379	W
		$T_C = 100\text{ }^\circ\text{C}$	152	W
Operating Junction Temperature	T_{vj}	-55 ~ 150	$^\circ\text{C}$	
Storage Temperature Range	T_{STG}	-55 ~ 150	$^\circ\text{C}$	
Maximum lead temperature for soldering purposes,	T_L	300	$^\circ\text{C}$	

Thermal Characteristics

Parameter	Symbol	Value	Unit
Maximum Thermal resistance, Junction-to-Case	R_{JC} (IGBT)	0.33	$^\circ\text{C/W}$
Maximum Thermal resistance, Junction-to-Case	R_{JC} (DIODE)	1.59	$^\circ\text{C/W}$
Maximum Thermal resistance, Junction-to-Ambient	R_{JA}	40	$^\circ\text{C/W}$

Electrical Characteristics of the IGBT $T_{vj}=25$, unless otherwise noted

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit
OFF						
Collector Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0V, I_C = 1mA$	900	--	--	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 900V, V_{GE} = 0V$	--	--	1	mA
Gate Emitter Leakage Current	I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 25V$	--	--	± 500	nA
ON						
Gate Emitter Threshold Voltage	$V_{GE(TH)}$	$V_{GE} = V_{CE}, I_C = 40mA$	4.5	6.5	7.5	V
Collector Emitter Saturation Voltage	$V_{CE(SAT)}$	$V_{GE} = 15V, I_C = 40A, T_{vj} = 25^\circ C$	--	2.0	2.5	V
		$V_{GE} = 15V, I_C = 40A, T_{vj} = 150^\circ C$	--	2.4	--	V
DYNAMIC						
Input Capacitance	C_{IES}	$V_{CE} = 30V,$ $V_{GE} = 0V$ $f = 1MHz$	--	3760	--	pF
Output Capacitance	C_{OES}		--	90	--	pF
Reverse Transfer Capacitance	C_{RES}		--	55	--	pF
SWITCHING (Note 2)						
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 40A$ $R_G = 5\ \Omega, V_{GE} = 15V$ Inductive Load, $T_{vj} = 25^\circ C$	--	35	--	ns
Rise Time	t_r		--	40	--	ns
Turn-Off Delay Time	$t_{d(off)}$		--	152	--	ns
Fall Time	t_f		--	25	--	ns
Turn-On Switching Loss	E_{ON}		--	6.3	9.5	mJ
Turn-Off Switching Loss	E_{OFF}		--	1.1	1.6	mJ
Total Switching Loss	E_{TS}		--	7.4	11.1	mJ
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 40A$ $R_G = 5\ \Omega, V_{GE} = 15V$ Inductive Load, $T_{vj} = 150^\circ C$	--	35	--	ns
Rise Time	t_r		--	36	--	ns
Turn-Off Delay Time	$t_{d(off)}$		--	156	--	ns
Fall Time	t_f		--	26	--	ns
Turn-On Switching Loss	E_{ON}		--	7.2	10.7	mJ
Turn-Off Switching Loss	E_{OFF}		--	1.5	2.2	mJ
Total Switching Loss	E_{TS}		--	8.6	13.0	mJ
Total Gate Charge	Q_g	$V_{CC} = 600V, I_C = 40A$ $V_{GE} = 15V$	--	210	315	nC
Gate-Emitter Charge	Q_{ge}		--	28	42	nC
Gate-Collector Charge	Q_{gc}		--	105	158	nC

Not subject to production test verified by design/characterization

Electrical Characteristics of the DIODE $T_{vj}=25$, unless otherwise noted

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit
Diode Forward Voltage	V_{FM}	$I_F = 40A, T_{vj} = 25\text{ }^\circ\text{C}$	--	2.3	--	V
		$I_F = 40A, T_{vj} = 150\text{ }^\circ\text{C}$	--	2.5	--	V
Reverse Recovery Time	t_{rr}	$I_F = 40A,$ $di/dt = 200A/\mu s,$ $T_{vj} = 25\text{ }^\circ\text{C}$	--	300	--	ns
Reverse Recovery Current	I_{rr}		--	30	--	A
Reverse Recovery Charge	Q_{rr}		--	5300	--	nC
Reverse Recovery Time	t_{rr}	$I_F = 40A,$ $di/dt = 200A/\mu s,$ $T_{vj} = 150\text{ }^\circ\text{C}$	--	380	--	ns
Reverse Recovery Current	I_{rr}		--	40	--	A
Reverse Recovery Charge	Q_{rr}		--	7540	--	nC

IGBT Characteristics

Fig. 1 IGBT Output Characteristics

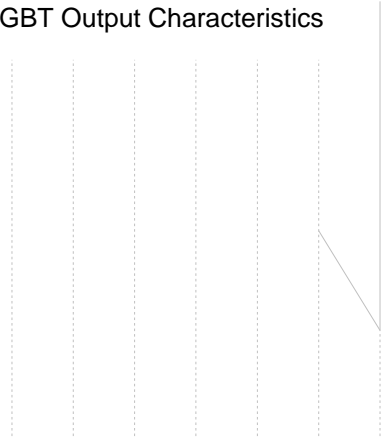


Fig. 2 IGBT Output Characteristics

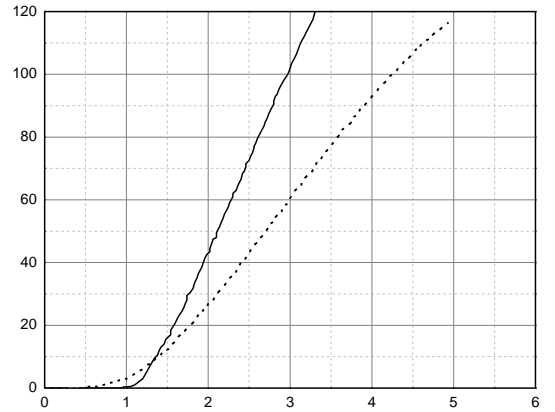


Fig. 3 IGBT Saturation Voltage vs. Junction Temperature

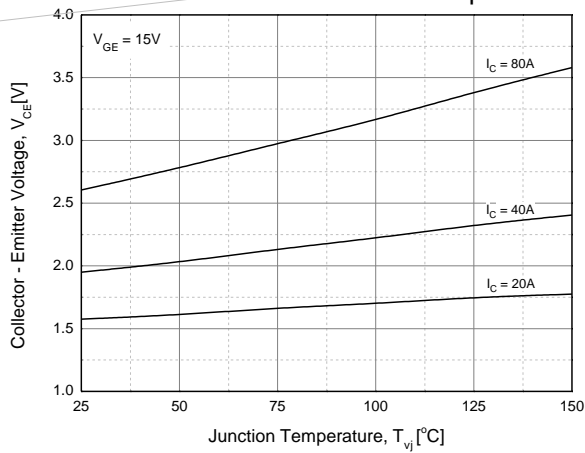


Fig. 4 IGBT Saturation Voltage vs. Gate Bias

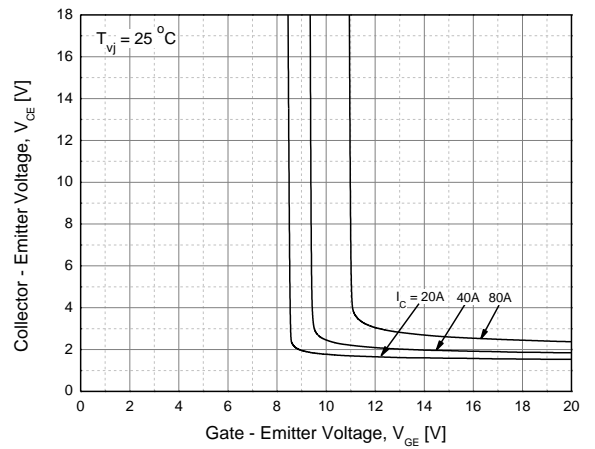


Fig. 5 IGBT Saturation Voltage vs. Gate Bias

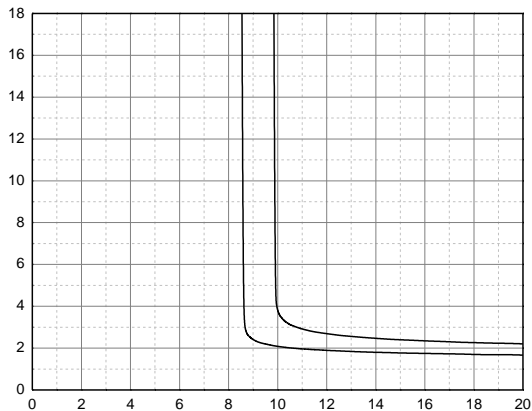
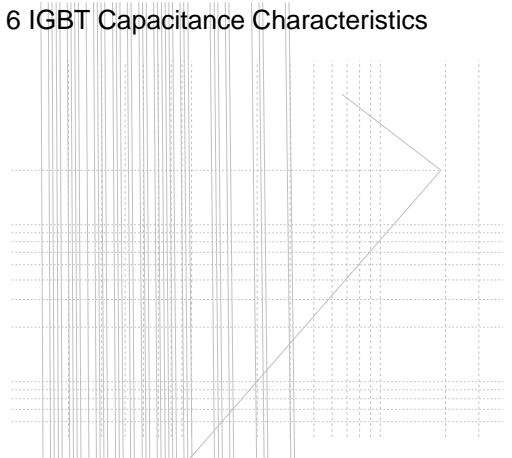


Fig. 6 IGBT Capacitance Characteristics



IGBT Characteristics

Fig. 7 Turn-on Time vs. Gate Resistor

Fig. 8 Turn-off Time vs. Gate Resistor

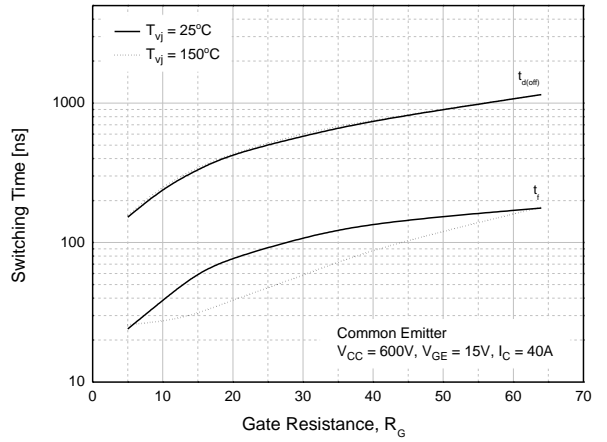


Fig. 9 Switching Loss vs. Gate Resistor

Fig. 10 Turn-on Time vs. Collector Current

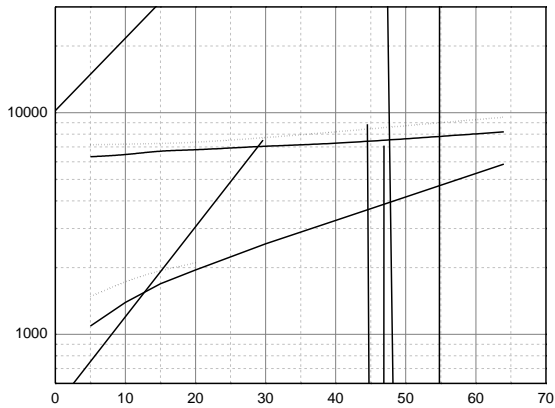


Fig. 11 Turn-off Time vs. Collector Current

Fig. 12 Switching Loss vs. Collector Current

IGBT Characteristics

Fig. 13 Gate Charge Characteristics

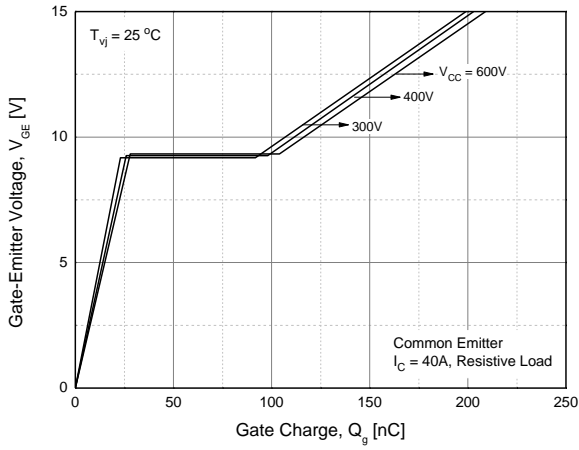


Fig. 14 SOA

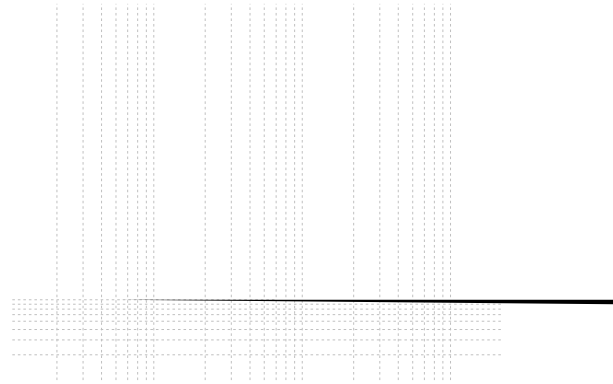


Fig. 15 RBSOA

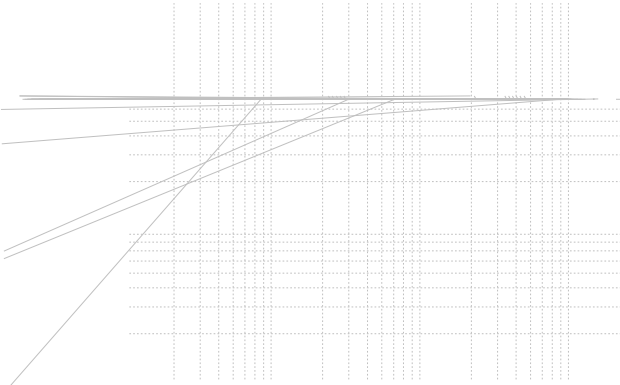


Fig. 16 Transient Thermal Impedance of IGBT

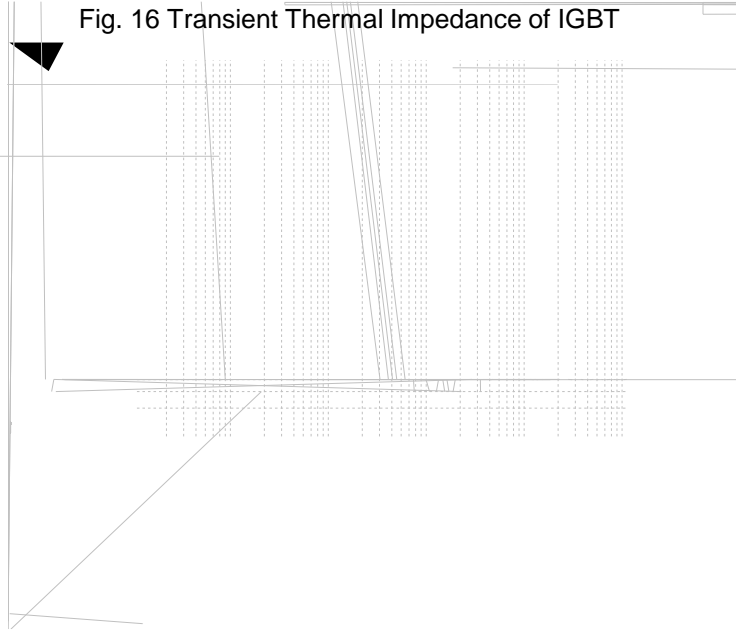


Fig. 17 Load Current vs. Frequency



Diode Characteristics

Fig. 18 Diode Conduction Characteristics

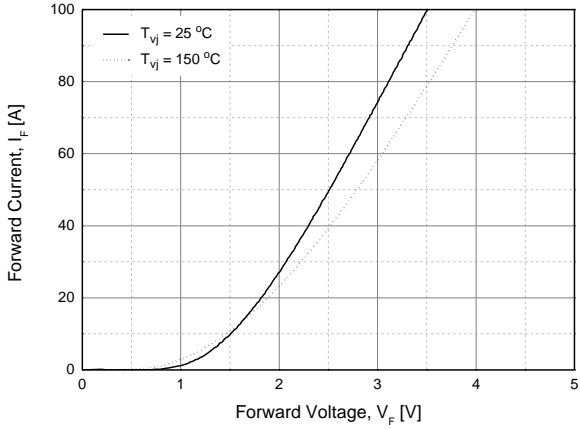


Fig. 19 Reverse Recovery Current vs. Forward Current

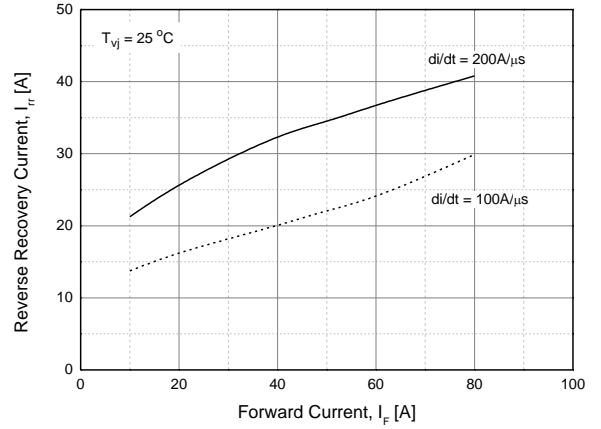


Fig. 20 Reverse Recovery Charge vs. Forward Current

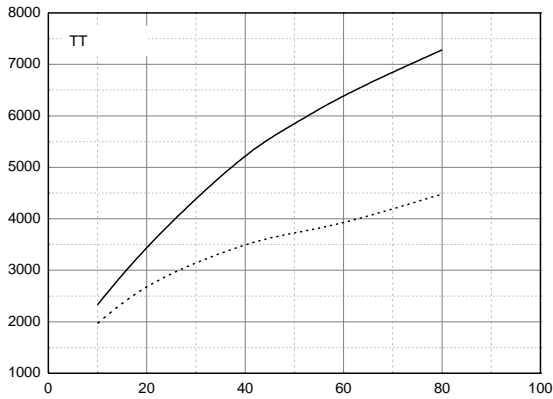
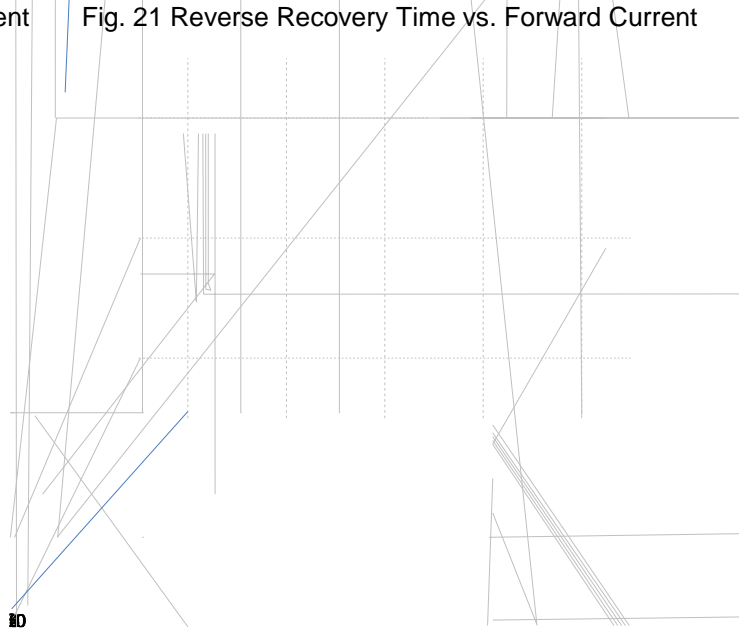
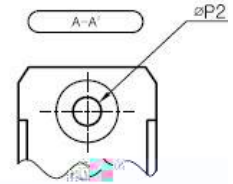
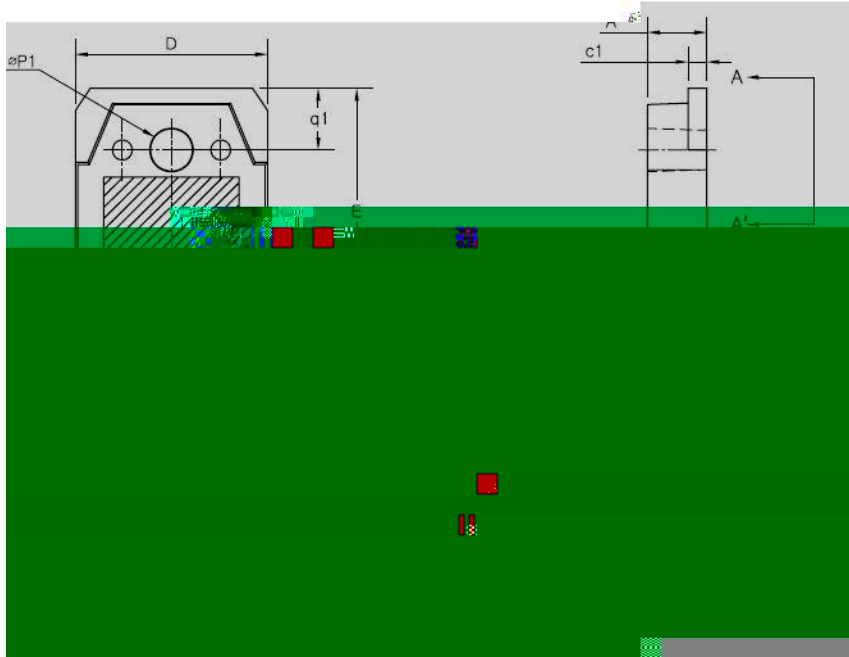


Fig. 21 Reverse Recovery Time vs. Forward Current



TO-3PN MECHANICAL DATA



SYMBOL	MIN	NOM	MAX
A	4.60	4.80	5.00
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.55	0.60	0.75
c1	1.45	1.50	1.65
D	15.40	15.60	15.80
E	19.70	19.90	20.10
e	5.15	5.45	5.75
L1	3.30	3.50	3.70
L2	19.80	20.00	20.20
øP1	3.30	3.40	3.50
øP2		(3.20)	
Q		2.40	2.60
q1	4.80	5.00	5.20

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